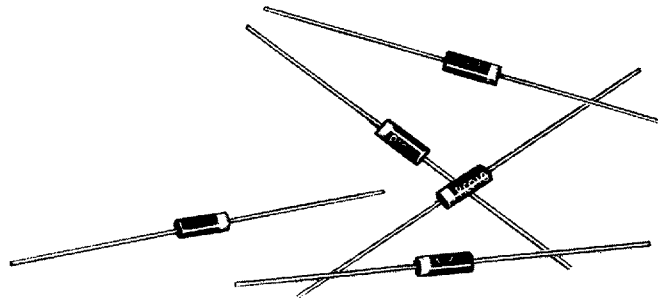


FAST RECOVERY 200 NANOSECOND SILICON RECTIFIER

- SMALL SIZE
- LOW LEAKAGE
- HIGH TEMPERATURE STABILITY
- HIGH SURGE CAPABILITY



EDI Type	PRV Volts	Maximum Reverse RECOVERY TIME IN NANoseconds (Fig. 4)
RC05	50	200
RC10	100	200
RC20	200	200
RC40	400	200
RC60	600	200
RC80	800	200
RC100	1000	200

ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

Average Rectified Forward Current @ 50°C , I_O	1 Amp
Max. Peak Surge Current, I_{FSM} (8.3ms)	50 Amp
Max. Forward Voltage Drop @ 1 Amp, V_F	1.4 Volts
Max. DC Reverse Current @PRV and 25°C , I_R	$1\mu\text{A}$
Max. DC Reverse Current @PRV and 100°C , I_R	$50\mu\text{A}$
Ambient Operating Temperature Range, T_A	-55°C to $+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55°C to $+175^\circ\text{C}$

NOTE:

Maximum lead and terminal temperature for soldering, 3/8 inch from case, 5 seconds at 260°C



ELECTRONIC DEVICES, INC.

21 GRAY OAKS AVENUE • YONKERS, NEW YORK 10710
914-965-4400 • FAX 914-965-5531 • 1-800-678-0828



FIG. 1

OUTPUT CURRENT vs AMBIENT TEMPERATURE

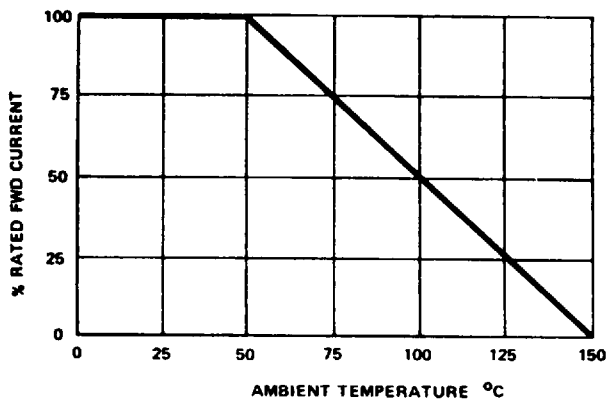


FIG. 2

NON - REPETITIVE SURGE CURRENT

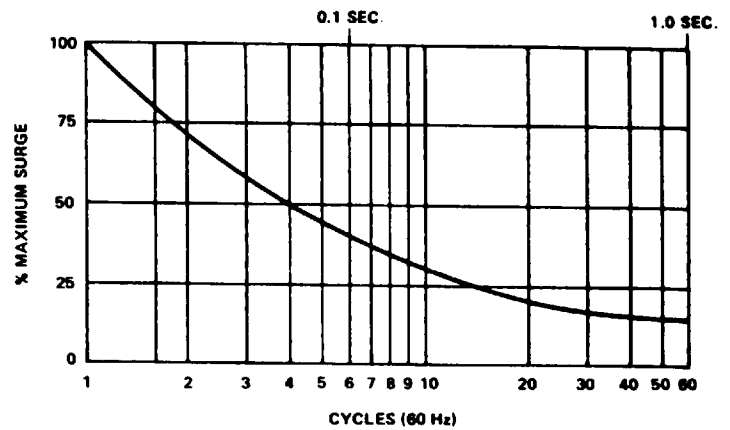
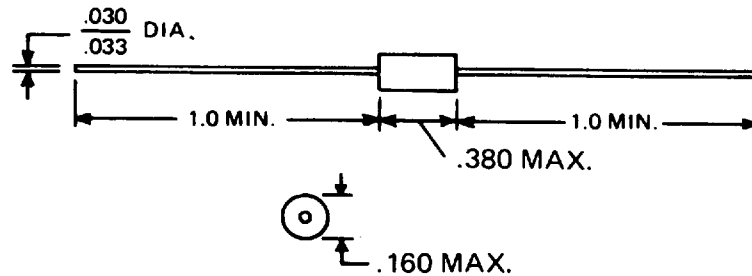


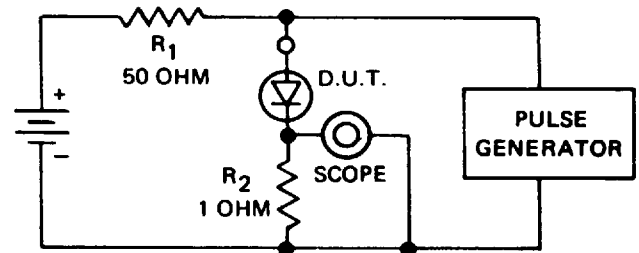
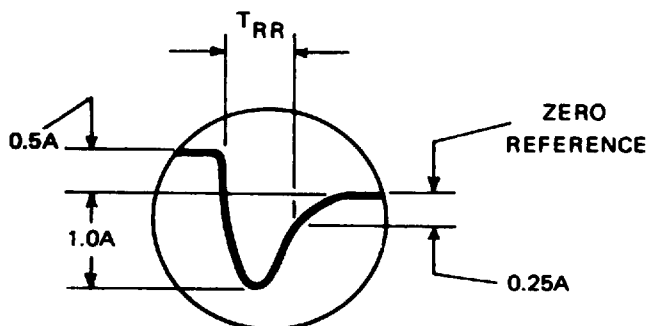
FIG. 3



TEST CIRCUIT

FIG. 4

TYPICAL REVERSE RECOVERY WAVEFORM



R₁, R₂ NON-INDUCTIVE RESISTORS
 PULSE GENERATOR - HEWLETT PACKARD 214A OR EQUIV.
 IKC REP. RATE, 10 μ SEC. PULSE WIDTH
 ADJUST PULSE AMPLITUDE FOR PEAK I_R

EDI reserves the right to change these specifications at any time without notice.

ELECTRONIC DEVICES, INC. DESIGNERS AND MANUFACTURERS OF SOLID STATE DEVICES SINCE 1951

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